## In the Claims:

Please cancel Claims 1-13 and amend Claim 18 as indicated below. The status of all claims is as follows:

## 1-13. (Cancelled)

14. (Original) A thin film transistor substrate comprising: a substrate;

a first transistor structure having a first semiconductor layer formed on said substrate, a first gate insulating film and a first gate electrode, wherein a channel region of said first semiconductor layer under said first gate electrode is intentionally doped with only p-type impurities, said first semiconductor layer includes n-type LDD regions outside the channel region and high impurity concentration n-type source/drain regions outside the n-type LDD regions, and said first gate electrode is made of a lamination of a first metal layer and a second metal layer;

a second transistor structure having a second semiconductor layer formed on said substrate, a second gate insulating film and a second gate electrode, wherein a channel region of said second semiconductor layer under said second gate electrode is intentionally doped with only p-type impurities, said second semiconductor layer includes high impurity

electrode is made of a lamination of said first metal layer and said second metal layer; and a third transistor structure having a third semiconductor layer formed on said substrate, a third gate insulating film and a third gate electrode, wherein a channel region of said third semiconductor layer under said third gate electrode is intentionally doped with p-type impurities and n-type impurities, said third semiconductor layer includes high impurity concentration p-type source/drain regions outside the channel region, and said third gate electrode is made of said second metal layer.

concentration n-type source/drain regions outside the channel region, and said second gate

- 15. (Original) The thin film transistor substrate according to claim 14, wherein said second semiconductor layer has n-type LDD regions outside the channel region, and the high impurity concentration n-type source/drain regions outside the n-type LDD regions.
- 16. (Original) The thin film transistor substrate according to claim 14, wherein said first and second metal layers have different etching characteristics.
- 17. (Original) The thin film transistor substrate according to claim 16, wherein said first metal layer is a refractory metal layer and said second metal layer is an aluminum alloy layer.

18. (Currently Amended) A thin film transistor substrate comprising: a substrate;

a first transistor structure having a first semiconductor layer formed on said substrate, a first gate insulating film and a first gate electrode, wherein a channel region of said first semiconductor layer under said first gate electrode is intentionally doped with only p-type impurities, said first semiconductor layer includes n-type LDD regions outside the channel region and high impurity concentration n-type source/drain regions outside the n-type LDD regions, and said first gate electrode is made of a second metal layer;

a second transistor structure having a second semiconductor layer formed on said substrate, a second gate insulating film and a second gate electrode, wherein a channel region of said second semiconductor layer under said second gate electrode is intentionally doped with p-type impurities at the first impurity concentration, said second semiconductor layer includes high impurity concentration n-type source/drain regions outside the channel region, and said second gate electrode is made of said second metal layer; and

a third transistor structure having a third semiconductor layer formed on said substrate, a third gate insulating film and a third gate electrode, wherein a channel region of said third semiconductor layer under said third gate electrode is intentionally doped with p-type impurities at a second impurity concentration lower than the first impurity concentration, said third semiconductor layer includes high impurity concentration p-type source/drain

regions outside the channel region, and said third gate electrode is made of a first second metal layer that is different from said first metal layer.

- 19. (Original) The thin film transistor substrate according to claim 18, wherein said second semiconductor layer has n-type LDD regions outside the channel region, and the high impurity concentration n-type source/drain regions outside the n-type LDD regions.
- 20. (Original) The thin film transistor substrate according to claim 18, wherein said first metal layer has etching characteristics different from those of said second metal layer.
- 21. (Original) The thin film transistor substrate according to claims 20, wherein said first metal layer is a refractory metal layer and said second metal layer is an aluminum alloy layer.